

3DK106, 3DK108**NPN Silicon High Frequency Moddle Power Switch Transistor****Features:**

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation and high frequency switch, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							
			3DK106				3DK108			
			A	B	C	D	A	B	C	D
Total Dissipation	P_{tot}	mW	700 (Ta=25°C)				1000 (Ta=25°C)			
Max. Collector Current	I_{CM}	mA	600				1000			
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	40	60	40	60	40	60	40	60
			Ic=0.1mA							
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	30	45	30	45	30	45	30	45
			Ic=0.1mA							
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	≥4 (IE=0.1 mA)							
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5 (Ic=500mA, Ib=50mA)							
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.2 (Ic=500mA, Ib=50mA)							
C-E Leakage Current	I_{CEO}	uA	1.0 (VCE=20V)							
DC Current Gain	h_{FE}		Orange:25~40, Yellow:40~55, Green:55~80, Blue:80~120, Purple:120~180							
			(VCE=1V, Ic=500mA)							
Transition frequency	f_T	MHz	150 (VCE=10V, Ic=50mA, f=100MHz)				200 (VCE=10V, Ic=100mA, f=100MHz)			
Turn-on Time	Ic=300 mA Ib1= Ib2=30mA	ton	30				30			
Storage Time		ts	250		100		250		100	
Fall Time		tf	30				30			

Outline and Dimensions: